

What is claimed is:

1. A method for inspecting contact hole after contact etching, said method comprising the steps of:

performing an SEM electron beam scanning on the wafer after contact
5 etching; and

comparing color of said a plurality of contact holes represented on the SEM photograph, if said a plurality of contact holes display different color which means some of said a plurality of contact holes etching abnormal.

10 2. The method of claim 1, wherein said a plurality of contact holes display different color means if said a plurality of contact holes etching process is normal, said a plurality of contact holes will display white color on the SEM photograph. If said a plurality of contact holes etching process is abnormal, said a plurality of contact holes will display dark color on the SEM photograph. If said a plurality of
15 contact holes are partial etched, said a plurality of contact holes will display irregular white color on the SEM photograph..

20 3. The method of claim 1, wherein said performing an SEM electron beam scanning amplification factor is 500 to 5K.

4. A method for inspecting a contact hole after contact etching, said method comprising the steps of:

performing an SEM electron beam scanning on the wafer after contact etching; and

comparing color of said a plurality of contact holes represented on the SEM photograph;

etching process of contact holes is normal if said a plurality of contact holes display white color on the SEM photograph; and

5 etching process of contact holes is abnormal if said a plurality of contact holes display dark color or irregular white color on the SEM photograph.

5. The method of claim 4, wherein said performing an SEM electron beam scanning amplification factor is 500 to 5K.

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